

Vishay Siliconix

0.4- Ω Low-Voltage Dual SPDT Analog Switch

DESCRIPTION

The DG2531/DG2532 is a sub 1- Ω (0.4 Ω at 2.7 V) dual SPDT analog switches designed for low voltage applications.

The DG2531/DG2532 has on-resistance matching (less than 0.05 Ω at 2.7 V) and flatness (less than 0.2 Ω at 2.7 V) that are guaranteed over the entire voltage range. Additionally, low logic thresholds makes the DG2531/DG2532 an ideal interface to low voltage DSP control signals.

The DG2531/DG2532 has fast switching speed (on/off time at 40 and 35 ns) with break-before-make guaranteed. In the On condition, all switching elements conduct equally in both directions. Off-isolation and crosstalk is - 69 dB at 100 kHz.

The DG2531/DG2532 is built on Vishay Siliconix's high-density low voltage CMOS process. An eptiaxial layer is built in to prevent latchup. The DG2531/DG2532 contains the additional benefit of 2000 V ESD protection.

Packaged in space saving MSOP-10, the DG2531/DG2532 is a high performance, low $r_{\rm ON}$ switches for battery powered applications.

FEATURES

- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance r_{ON}: 0.4 Ω at 2.7 V
- - 69 dB OIRR at 2.7 V, 100 kHz
- MSOP-10 Package
- ESD Protection > 2000 V

BENEFITS

- Reduced Power Consumption
- High Accuracy
- Reduce Board Space
- 1.6 V Logic Compatible
- High Bandwidth

APPLICATIONS

- Cellular Phones
- Speaker Headset Switching
- Audio and Video Signal Routing
- PCMCIA Cards
- Battery Operated Systems
- Relay Replacement

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





Top View

GND

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TRUTH TABLE					
Logic	NC1 and NC2	NO1 and NO2			
0	ON	OFF			
1	OFF	ON			

ORDERING INFORMATION				
Temp Range	Package	Part Number		
- 40 to 85 °C	MSOP-10	DG2531DQ-T1-E3 DG2532DQ-T1-E3		



COMPLIANT

NO1

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ABSOLUTE MAXIMUM RATINGS					
Parameter		Limit	Unit		
Reference V+ to GND		- 0.3 to + 6	V		
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	v		
Continuous Current (NO, NC, COM)		± 300	mA		
Peak Current (Pulsed at 1 ms, 10 % du	Peak Current (Pulsed at 1 ms, 10 % duty cycle)		IIIA		
Storage Temperature	(D Suffix)	- 65 to 150	°C		
PESD per Method 3015.7		> 2	kV		
Power Dissipation (Packages) ^b	MSOP-10 ^c	320	mW		

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
b. All leads welded or soldered to PC Board.
c. Derate 4.0 mW/°C above 70 °C.

SPECIFICATIONS (V+ = 3 V)							
		Test Conditions Otherwise Unless Specified		Limits - 40 to 85 °C			
Parameter	Symbol	V+ = 3 V, \pm 10 %,V $_{\rm IN}$ = 0.5 V or 1.4 V $^{\rm e}$	Temp ^a	Min ^b	Тур ^с	Max ^b	Unit
Analog Switch				•	•	•	
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	v
On-Resistance	r _{ON}	V+ = 2.7 V, V _{COM} = 0.6 V/1.5 V I _{NO} , I _{NC} = 100 mA	Room Full		0.4	0.6 0.7	
r _{ON} Flatness ^d	r _{ON} Flatness		Room		0.12	0.2	Ω
On-Resistance Match Between Channels ^d	$\Delta r_{DS(on)}$		Room			0.05	
	I _{NO(off)} I _{NC(off)}	V+ = 3.3 V, V _{NO} , V _{NC} = 0.3 V/3 V, V _{COM} = 3 V/0.3 V	Room Full	- 1 - 10		1 10	nA
Switch Off Leakage Current	I _{COM(off)}		Room Full	- 1 - 10		1 10	
Channel-On Leakage Current	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 0.3 V/3 V	.3 V/3 V Room - 1 Full - 10	1 10			
Digital Control							
Input High Voltage ^d	V _{INH}		Full	1.4			v
Input Low Voltage	V _{INL}		Full			0.5	
Input Capacitance	C _{in}		Full		7		pF
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0$ or V+	Full	1		1	μA



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SPECIFICATIONS (V+ = 3 V)							
		Test Conditions Otherwise Unless Specified		Limits - 40 to 85 °C			
Parameter	Symbol	V+ = 3 V, \pm 10 %,V_{IN} = 0.5 V or 1.4 V e	Temp ^a	Min ^b	Тур ^с	Max ^b	Unit
Dynamic Characteristics							
Turn-On Time	t _{ON}	V _{NO} or V _{NC} = 2.0 V, R _L = 50 Ω, C _L = 35 pF	Room Full		40	70 77	
Turn-Off Time	t _{OFF}		Room Full		35	65 72	ns
Break-Before-Make Time	t _d		Room	1	4		
Charge Injection ^d	Q _{INJ}	C_{L} = 1 nF, V_{GEN} = 1.5 V, R_{GEN} = 0 Ω	Room		54		рС
Off-Isolation ^d	OIRR	R _I = 50 Ω, C _I = 5 pF, f = 100 kHz	Room		- 69		dB
Crosstalk ^d	X _{TALK}	n_ = 30 sz, 0_ = 3 pr, r = 100 ki iz	Room		- 69		UD
N_O , N_C Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		143		pF
Channel-On Capacitance ^d	C _{NO(on)} C _{NC(on)}		Room		403		יק
Power Supply							
Power Supply Range	V+			1.8		5.5	V
Power Supply Current	l+	V _{IN} = 0 or V+	Full			1.0	μA

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.
b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet. d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS $T_A = 25 \text{ °C}$, unless otherwise noted





Temperature (°C)







r_{ON} vs. Analog Voltage and Temperature (NC1)



Supply Current vs. Input Switching Frequency





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TEST CIRCUITS









Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.



Logic

Input

 $V_{NC} = V_{NO}$

Switch 0 V

Output

 V_{INH}

 V_{INL}

Vo

90 %

t_D



CL (includes fixture and stray capacitance)







IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection



t_r < 5 ns t_f < 5 ns

t_D



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TEST CIRCUITS



Figure 4. Off-Isolation



Figure 5. Channel Off/On Capacitance

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